MGBR20L60C

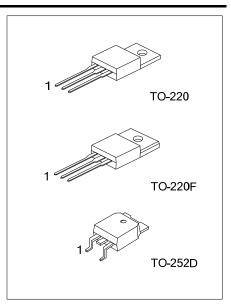
# DUAL MOS GATED BARRIER RECTIFIERS

#### **■** DESCRIPTION

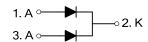
The UTC MGBR20L60C is a dual mos gated barrier rectifiers, it uses UTC's advanced technology to provide customers with high current capability, low forward voltage and high switching speed, etc.

#### **■ FEATURES**

- \* Low forward voltage
- \* High switching speed
- \* High current capability



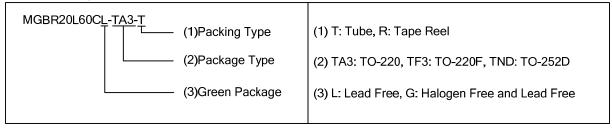
## ■ SYMBOL



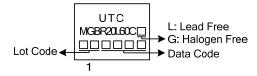
### ■ ORDERING INFORMATION

| Ordering Number   |                                     | Dookogo | Pin Assignment |   |   | Dooking   |  |
|-------------------|-------------------------------------|---------|----------------|---|---|-----------|--|
| Lead Free         | Halogen Free                        | Package | 1              | 2 | 3 | Packing   |  |
| MGBR20L60CL-TA3-T | MGBR20L60CL-TA3-T MGBR20L60CG-TA3-T |         | Α              | K | Α | Tube      |  |
| MGBR20L60CL-TF3-T | MGBR20L60CG-TF3-T                   | TO-220F | Α              | K | Α | Tube      |  |
| MGBR20L60CL-TND-R | MGBR20L60CG-TND-R                   | TO-252D | Α              | K | Α | Tape Reel |  |

Note: Pin Assignment: A: Anode K: Common Cathode



## MARKING



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MGBR20L60C DIODE

# ■ **ABSOLUTE MAXIMUM RATINGS** (T<sub>A</sub>=25°C unless otherwise specified)

| PARAMETER                         |         | SYMBOL           | RATINGS  | UNIT |
|-----------------------------------|---------|------------------|----------|------|
| DC Blocking Voltage               |         | $V_{RM}$         | 60       | V    |
| Working Peak Reverse Voltage      |         | $V_{RWM}$        | 60       | V    |
| Peak Repetitive Reverse Voltage   |         | $V_{RRM}$        | 60       | ٧    |
| Average Rectified Forward Current | Per Leg | Io               | 10       | Α    |
|                                   | Total   |                  | 20       | Α    |
| Peak Forward Surge Current        |         | I <sub>FSM</sub> | 150      | Α    |
| Operating Junction Temperature    |         | $T_J$            | -65~+150 | Ô    |
| Storage Temperature               |         | T <sub>STG</sub> | -65~+150 | °C   |

Note: Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.

#### ■ THERMAL DATA

| PARAMETER .         |                | SYMBOL          | RATINGS | UNIT |  |
|---------------------|----------------|-----------------|---------|------|--|
| Junction to Ambient | TO-220/TO-220F | θ <sub>JA</sub> | 62.5    | °C/W |  |
|                     | TO-252D        |                 | 110     |      |  |
| Junction to Case    | TO-220         | θ <sub>ЈС</sub> | 2       | °C/W |  |
|                     | TO-220F        |                 | 3.31    |      |  |
|                     | TO-252D        |                 | 2.5     |      |  |

# ■ **ELECTRICAL CHARACTERISTICS** (T<sub>A</sub> =25°C unless otherwise specified.)

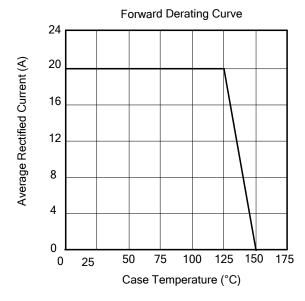
| PARAMETER                              | SYMBOL          | TEST CONDITIONS                             | MIN | TYP  | MAX  | UNIT |
|--|-----------------|---|-----|------|------|------|
| Reverse Breakdown Voltage (Note 1)     | $V_{(BR)R}$     | I <sub>R</sub> =0.50mA                      | 60  |      |      | V    |
| Instantaneous Forward Voltage          | V <sub>FM</sub> | I <sub>F</sub> =5A, T <sub>J</sub> =25°C    |     | 0.46 |      | V    |
|  |                 | I <sub>F</sub> =5A, T <sub>J</sub> =125°C   |     | 0.41 |      | V    |
|  |                 | I <sub>F</sub> =10A, T <sub>J</sub> =25°C   |     |      | 0.64 | ٧    |
|  |                 | I <sub>F</sub> =10A, T <sub>J</sub> =125°C  |     |      | 0.59 | V    |
| Instantaneous Reverse Current (Note 1) | DM              | V <sub>RM</sub> =60V, T <sub>J</sub> =25°C  |     |      | 300  | μΑ   |
|  |                 | V <sub>RM</sub> =60V, T <sub>J</sub> =125°C |     |      | 20   | mA   |

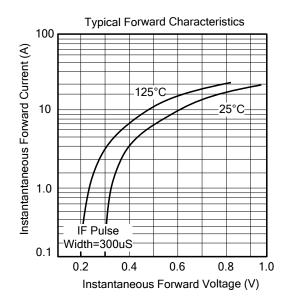
Notes: 1. Short duration pulse test used to minimize self-heating effect.

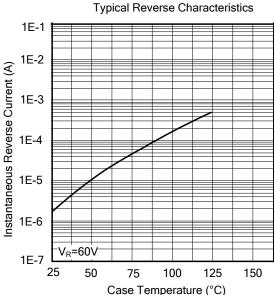
<sup>2.</sup> Thermal resistance junction to case mounted on heatsink.

MGBR20L60C DIODE

## **■ TYPICAL CHARACTERISTICS**







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